

## SMD Type

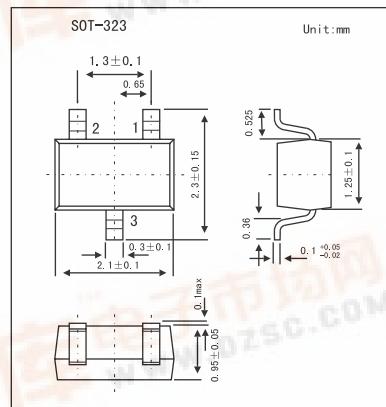
Diodes

## Silicon Schottky Diodes

**BAS125W;BAS125-04W  
BAS125-05W;BAS125-06W**

### ■ Features

- For low-loss, fast-recovery, meter protection, bias isolation and clamping application
- Integrated diffused guard ring
- Low forward voltage



### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Diode reverse voltage	V <sub>R</sub>	25	V
Forward current	I <sub>F</sub>	100	mA
Surge forward current (t ≤ 10ms)	I <sub>FSM</sub>	500	mA
Total Power dissipation Ts ≤ 25°C	P <sub>tot</sub>	250	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-50 to +150	°C
Junction ambient BAS125W (Note 1)	R <sub>thJA</sub>	≤ 310	K/W
Junction ambient BAS125-04W...06W (Note 1)	R <sub>thJA</sub>	≤ 425	K/W
Junction - soldering point BAS125W	R <sub>thJS</sub>	≤ 230	K/W
Junction - soldering point BAS125-04W...06W	R <sub>thJS</sub>	≤ 265	K/W

## Note

Package mounted on alumina 15mm × 16.7mm × 0.7mm

### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 20 V			150	nA
		V <sub>R</sub> = 25 V			200	
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 1 mA		385	400	mV
		I <sub>F</sub> = 10 mA		530	650	
		I <sub>F</sub> = 35 mA		800	900	
Diode capacitance	C <sub>T</sub>	V <sub>R</sub> = 0 V, f = 1 MHz			1.1	pF
Differential forward resistance	R <sub>F</sub>	I <sub>F</sub> = 5 mA, f = 10 KHz		16		Ω

### ■ Marking

Type	BAS125W	BAS125-04W	BAS125-05W	BAS125-06W
Marking	13s	14s	15s	16s